

## Mask Process Modeling in the Multi-beam Era



Managing Company Sponsor

**D2S Patented Technology** 



#### eBeam Initiative, SPIE 2017

## **Questions About the New Mask-Writing Era**



- What's different about the multi-beam era?
- What's the same?
- What do we need to consider when modeling a multi-beam system?
- Mask process modeling in the multi-beam era

# $D_{2S}^{\circ}$ What's different about multi-beam?

**D2S Patented Technology** 

## **Multi-beam Uses Many Beamlets in Parallel**





Source: IMS Nanofabrication



## **Huge Opportunity to Make Masks Great**

- Any shape can be written in the same write time
- Dose profiles can be optimized





#### Multi-beam era moves us into the curvilinear domain!



## What will remain the same?

**D2S Patented Technology** 

## Mask Process Physics is the Same...



## ...Just More Complex







## What do we need to consider when modeling a multi-beam system?

**D2S Patented Technology** 

## Printed Mask Data Contains Both Shape and Dose Effects



We need to separate dose from shape effects!

## **Today:** Dose Models Used for Shape Correction <sup>D2S</sup>





are degenerate with the variable etch bias

.....



### **Printed Mask Data Contains Both Shape and Dose**





Only dose effects

#### Test structures needed to separate dose from shape effects!

## **Today's Simple Models are not Sufficient**

Non-zero y-axis values mean: mask print errors from model



Best fit "3G + constant threshold" model: Still 14nm of error!

- Fit overcompensates for the dose profile effects (3x dose)
- Fails to fully compensate for the small CD effect
- Demonstrates broken shape and dose degeneracies in the multi-beam era

## Standard 3G Models Do Not Predict Resist Data

Non-zero y-axis values mean: mask print errors from model



Best fit "3G + constant threshold" model

- Better, but still does not meet requirements
- Overall dose trends better
- Remember: there is more physics than simple scattering terms...

## **Dose-Specific Physics are Required**

Non-zero y-axis values mean: mask print errors from model



It is possible to make more physical models that meet desired tolerances Just need to add the correct physics.



## **Multi-beam Era is More Complicated**

VSB	Multi-beam
Dose profiles are "simple"	Dose profiles will be complex
Typically only "1" or "2" doses to worry about	Many dose values to predict
Can use dose terms <n>G to assist bias terms.</n>	Dose terms no longer degenerate to Etch terms; more complex dose models are needed
Etch done on rectilinear shapes	Etch needs to be done on curvilinear shapes



Bias models based on 1D data are under-constrained Shape effects depend on:

- Open area "shadowing"
- Local pattern density "loading"
- Local radius of curvature

A good etch model needs to encompass a wide variety of 2D features

## TrueModel<sup>®</sup> Mask Modeling for the Multi-beam Era



## Multi-beam Era Requires Dose + Shape Models

- The underlying physics is the same for VSB and multi-beam systems
  - We \*do\* need to start paying attention to the dose profiles
  - We \*do\* need to augment the simple shape effect model.
  - Challenge: isolate and model both dose and shape effects
- We do need to ensure a dose-aware model
- We will need to model this on curvilinear systems
- TrueModel has a test chip ideally suited for the new regime

## **TrueModel Understands Dose/Shape Separation** <sup>D<sub>2</sub>S/</sup>



### Printed Mask Data Contains Both Shape and Dose







Only dose effects

#### Test structures needed to separate dose from shape effects!

## TrueModel Predicts Shape Effects and Dose Effects Simultaneously

D<sub>2</sub>S

TrueModel results based on dose profile to resist data. 90nm of MTT can be brought to +/-2nm



### **TrueModel Predicts Both Shape and Dose Effects**



TrueModel results based on dose profile to resist data. 90nm of MTT can be brought to +/-2nm

## Model fit summary, including calibration data (circles) and prediction data (squares)



Modeling results correctly separate shape effects from dose effects...independent of tool

